

SCDS211B-AUGUST 2006-REVISED JUNE 2008

$0.75-\Omega$ SPDT ANALOG SWITCH WITH INPUT LOGIC TRANSLATION

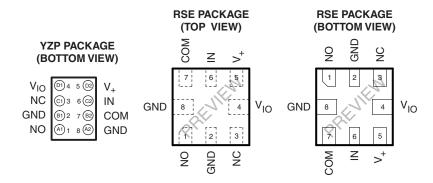
FEATURES

- Specified Break-Before-Make Switching
- Low ON-State Resistance (0.75 Ω Max)
- Control Inputs Referenced to VIO
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 2.25-V to 5.5-V Power Supply (V₊)
- 1.65-V to 1.95-V Logic Supply (V_{IO})
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 4000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
 - 400-V (YZP Package) / 250-V (RSE Package) Machine Model (A115-A)

- COM Port to GND
 - 8000-V Human-Body Model (A114-B, Class II)
 - ±15-kV Contact Discharge (IEC 61000-4-2)

APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation



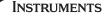
DESCRIPTION/ORDERING INFORMATION

The TS5A6542 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device offers a low ON-state resistance with an excellent channel-to-channel ON-state resistance matching, and the break-before-make feature to prevent signal distorion during the transferring of a signal from one path to another. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

The TS5A6542 has a separate logic supply pin (V_{IO}) that is characterized to operate from 1.65 V to 1.95 V. V_{IO} powers the control circuitry, which allows the TS5A6542 to be controlled by 1.8-V signals.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾		
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A6542YZPR	JH7		
	QFN – RSE	Tape and reel	TS5A6542RSER	PREVIEW		

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(3) YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

Configuration	2:1 Multiplexer/Demultiplexer (1 × SPDT)
Number of channels	1
ON-state resistance (ron)	0.75 Ω max
ON-state resistance match (Δr_{on})	0.1 Ω max
ON-state resistance flatness (ron(flat))	0.1 Ω max
Turn-on/turn-off time (t _{ON} /t _{OFF})	25 ns/20 ns
Charge injection (Q _C)	15 pC
Bandwidth (BW)	43 MHz
OFF isolation (O _{ISO})	–63 dB at 1 MHz
Crosstalk (X _{TALK})	–63 dB at 1 MHz
Total harmonic distortion (THD)	0.004%
Leakage current (I _{NO(OFF)} /I _{NC(OFF)})	20 nA
Package option	8-pin WCSP

SUMMARY OF CHARACTERISTICS⁽¹⁾

(1) $V_+ = 5 V, T_A = 25^{\circ}C$

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
н	OFF	ON

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ABSOLUTE MAXIMUM RATINGS⁽¹⁾⁽²⁾ over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊ V _{IO}	Supply voltage range ⁽³⁾		-0.5	6.5	V
V _{NC} V _{NO} V _{COM}	Analog voltage range ⁽³⁾⁽⁴⁾⁽⁵⁾		-0.5	V ₊ + 0.5	V
I _{I/OK}	Analog port diode current ⁽⁶⁾	V_{NO} , V_{COM} < 0 or V_{NO} , V_{COM} > V_{+}	-50	50	mA
I _{NC}	On-state switch current		-200	200	
I _{NO} I _{COM}	On-state peak switch current ⁽⁷⁾	$V_{\rm NO,} V_{\rm COM} = 0$ to V ₊	-400	400	mA
VI	Digital input voltage range ⁽³⁾⁽⁴⁾		-0.5	6.5	V
I _{IK}	Digital input clamp current	V _I < 0	-50		mA
I ₊ I _{GND}	Continuous current through V_+ or GNE)	-100	100	mA
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(3) All voltages are with respect to ground, unless otherwise specified.

(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(5) This value is limited to 5.5 V maximum.

(6) Requires clamp diodes on analog port to V₊

(7) Pulse at 1-ms duration < 10% duty cycle

THERMAL IMPEDANCE RATINGS

				UNIT
	Deckage thermal impedance ⁽¹⁾	RSE package	TBD	°C/W
(θ _{JA} Package thermal impedance ⁽¹⁾	YZP package	102	C/W

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

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ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾

V₊ = 4.5 V to 5.5 V, V_{IO} = 1.65 V to 1.95 V, T_A = -40° C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	٧.	MIN	TYP	MAX	UNIT	
Analog Switch										
Analog signal range	V _{COM} , V _{NO}					0		V+	V	
ON-state resistance	r	V_{NO} or $V_{NC} = 2.5 V$,		25°C	4.5 V		0.5	0.75	Ω	
ON-State resistance	r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full	4.5 V			0.8	32	
ON-state resistance	۸	V_{NO} or $V_{NC} = 2.5 V$,	Switch ON,	25°C	4.5 V		0.05	0.1	Ω	
match between channels	∆r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full	4.5 V			0.1	Ω	
ON-state resistance	_	$\begin{array}{l} 0 \leq (V_{NO} \text{ or } V_{NC}) \leq \\ V_{+}, \\ I_{COM} = -100 \text{ mA}, \end{array}$	Switch ON, See Figure 14	25°C	4.5 V		0.1		Ω	
flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 1 V$,	Switch ON,	25°C	4.5 V		0.1	0.25	12	
		1.5 V, 2.5 V, I _{COM} = -100 mA,	See Figure 14	Full				0.25		
		V _{NO} = 1 V, 4.5 V,		25°C		-20	2	20	nA	
NO, NC OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$ \begin{array}{l} V_{COM}^{C} = 4.5 \ V, \ 1 \ V, \\ V_{NC} = Open, \\ or \\ V_{NO} = 1 \ V, \ 4.5 \ V, \\ V_{COM} = 4.5 \ V, \ 1 \ V, \\ V_{NO} = Open, \end{array} $	Switch OFF, See Figure 15	Full	5.5 V	-100		100		
		$V_{NO} = 1 V, 4.5 V,$		25°C		-20	2	20		
NC, NO ON leakage current	I _{NO(ON)}	$\label{eq:VCOM} \begin{array}{l} V_{COM}, V_{NC} = Open, \\ or \\ V_{NC} = 1 V, 4.5 V, \\ V_{COM}, V_{NO} = Open, \end{array}$	Switch ON, See Figure 16	Full	5.5 V	-200		200	nA	
		$V_{COM} = 1 V, 4.5 V,$		25°C		-20	2	20		
COM ON leakage current	I _{COM(ON)}	$\label{eq:vno} \begin{array}{l} v_{NO} \text{ and } v_{NC} = \\ Open, \\ or \\ v_{COM} = 1 \ V, \ 4.5 \ V, \\ v_{NO} \ or \ V_{NC} = Open, \end{array}$	or See Figure To $V_{COM} = 1 \text{ V}, 4.5 \text{ V},$		5.5 V	-200		200	nA	
Digital Control Input (IN) ⁽²⁾					-				
Input logic high	V _{IH}	$V_{IO} = 1.65$ V to 1.95 V	V	Full		0.65 × V _{IO}		V _{IO}	V	
Input logic low	V _{IL}	$V_{\rm IO} = 1.65$ V to 1.95 V	V	Full		0		0.35 × V _{IO}	V	
Input leakage current	current I_{IH}, I_{IL} $V_I = V_{IO} \text{ or } 0$		25°C	5.5 V	-2		2	nA		
input loanage ourient			Full	0.0 V	-20		20	ПА		

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY (continued)

V₊ = 4.5 V to 5.5 V, V_{IO} = 1.65 V to 1.95 V, T_A = -40° C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	ONDITIONS	TA	۷.	MIN	TYP	MAX	UNIT
Dynamic	1			1	1	1			
Turn-on time	t _{ON}	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	5 V	1	12.5	25	ns
	ÖN	$R_L = 50 \Omega,$	See Figure 18	Full	4.5 V			30	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	5 V	1	9.5	20	ns
	OFF	$R_L = 50 \Omega,$	See Figure 18	Full	4.5 V			25	110
Break-before-make	t _{BBM}	$V_{\rm NC}=V_{\rm NO}=V_+/2,$	C _L = 35 pF,	25°C	5 V	1	5	10	ns
time	'BBM	$R_L = 50 \Omega$,	See Figure 19	Full	4.5 V	1		12	113
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	= 0, See Figure 23		5 V	15			рС
NO OFF capacitance	C _{NO(OFF)}	$V_{NO} = V_+ \text{ or GND},$ Switch OFF,	See Figure 17	25°C	5 V		37		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	5 V		130		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	5 V		130		pF
Digital input capacitance	CI	$V_{I} = V_{IO} \text{ or } GND,$	See Figure 17	25°C	5 V		6.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	5 V		43		MHz
OFF isolation	O _{ISO}	$\begin{array}{l} R_{L} = 50 \ \Omega, \\ f = 1 \ MHz, \end{array}$	See Figure 21	25°C	5 V		-63		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega,$ f = 1 MHz,	See Figure 22	25°C	5 V		-63		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	5 V		0.00 4		%
Supply									
Positive supply		V V ar OND		25°C	C /		5.5	100	0 0
current	I+	$V_I = V_{IO}$ or GND		Full	5.5 V			750	nA

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ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾

 V_{+} = 3 V to 3.6 V, V_{10} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDIT	IONS	TA	V+	MIN	TYP	MAX	UNIT	
Analog Switch										
Analog signal range	V _{COM} , V _{NO}					0		V+	V	
ON-state resistance	r _{on}	V_{NO} or $V_{NC} = 2 V$, $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 14	25°C Full	3 V		0.75	0.9 1.2	Ω	
ON-state resistance match between channels	Δr _{on}	$V_{NO} \text{ or } V_{NC} = 2 \text{ V}, 0.8 \text{ V}, \ I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C Full	3 V		0.1	0.15 0.15	Ω	
ON-state resistance		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C			0.2			
flatness	r _{on(flat)}	$V_{NO} \text{ or } V_{NC} = 0.8 \text{ V}, 2 \text{ V},$	Switch ON,	25°C	3 V		0.1	0.3	Ω	
		$I_{COM} = -100 \text{ mA},$	See Figure 14	Full				0.3		
		$V_{NO} = 1 V, 3 V,$		25°C		-20	2	20	20 50 nA	
NO, NC OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}		Switch OFF, See Figure 15	Full	3.6 V	-50		50		
		V _{NO} = 1 V, 3 V,		25°C		-10	2	10	10 30 nA	
NC, NO ON leakage current	I _{NO(ON)}	$\label{eq:VNC} \begin{array}{l} V_{NC} \text{ and } V_{COM} = \text{Open}, \\ \text{or} \\ V_{NC} = 1 \text{ V}, 3 \text{ V}, \\ V_{NO} \text{ and } V_{COM} = \text{Open}, \end{array}$	Switch ON, See Figure 16	Full	3.6 V	-30		30		
		$V_{COM} = 1 V,$		25°C		-10	2	10		
COM ON leakage current	I _{COM(ON)}	$\label{eq:VNO} \begin{array}{l} V_{NO} \text{ and } V_{NC} = Open, \\ \text{or} \\ V_{COM} = 3 \ \text{V}, \\ V_{NO} \text{ and } V_{NC} = Open, \end{array}$	See Figure 16	Full	3.6 V	-30		30	nA	
Digital Control Input (IN) ⁽²⁾									
Input logic high	V _{IH}	$V_{IO} = 1.65 \text{ V to } 1.95 \text{ V}$		Full		0.65 × V _{IO}		V _{IO}	V	
Input logic low	V _{IL}	$V_{\rm IO}$ = 1.65 V to 1.95 V		Full		0		0.35 × V _{IO}	V	
Input leakage current	I _{IH} , I _{IL}	$V_{I} = V_{IO} \text{ or } 0$		25°C Full	3.6 V	-2 -20		2 20	nA	

(1)

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, (2) Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY (continued)

V₊ = 3 V to 3.6 V, V_{IO} = 1.65 V to 1.95 V, $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	٧,	MIN	ТҮР	MAX	UNIT
Dynamic	1		La construction de la constructi		I				
Turn-on time	t _{ON}	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	3.3 V	5	15	30	ns
	0.1	$R_L = 50 \Omega,$	See Figure 18	Full	3 V	3		35	
Turn-off time	torr	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	3.3 V	1	9	20	ns
rum-on ume	t _{OFF}	$R_L = 50 \Omega$,	See Figure 18	Full	3 V	1		25	115
Break-before-make	t _{BBM}	$V_{\rm NC} = V_{\rm NO} = V_{+}/2,$	$C_{L} = 35 \text{ pF},$	25°C	3.3 V	1	8	13	ns
time	-DDIVI	$R_L = 50 \Omega,$	See Figure 19	Full	3 V	1		15	
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 23	25°C	3.3V		6.5		рС
NO OFF capacitance	C _{NO(OFF)}	$V_{NO} = V_+ \text{ or GND},$ Switch OFF,	See Figure 17	25°C	3.3 V		38		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	3.3 V		133		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_+ \text{ or GND},$ Switch ON,	See Figure 17	25°C	3.3 V		133		pF
Digital input capacitance	CI	$V_{I} = V_{IO}$ or GND,	See Figure 17	25°C	3.3 V		6.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	3.3 V		42		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega,$ f = 1 MHz,	See Figure 21	25°C	3.3 V		-63		dB
Crosstalk	X _{TALK}	$ \begin{array}{l} R_L = 50 \ \Omega, \\ f = 1 \ MHz, \end{array} $	See Figure 22	25°C	3.3 V		-63		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	3.3 V		0.00 4		%
Supply									
Positive supply				25°C	0.0.1/		10	50	
current	l+	$V_{I} = V_{IO} \text{ or } GND$	-	Full	3.6 V			300	nA

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Electrical Characteristics for 2.5-V Supply⁽¹⁾ $V_{+} = 2.25 \text{ V}$ to 2.75 V, $V_{IO} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDIT	IONS	TA	V.	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V _{COM} , V _{NO}					0		V+	V
ON-state resistance	r _{on}	V_{NO} or V_{NC} = 1.8 V, I_{COM} = -100 mA,	Switch ON, See Figure 14	25°C Full	2.25 V		1	1.3 1.6	Ω
ON-state resistance match between	Δr _{on}	$V_{NO} \text{ or } V_{NC} = 1.8 \text{ V},$ 0.8 V,	Switch ON,	25°C	2.25 V		0.15	0.2	Ω
channels	Δι _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full	2.23 V			0.2	32
ON-state resistance		$\begin{array}{l} 0 \leq (V_{\rm NO} \mbox{ or } V_{\rm NC}) \leq V_{+}, \\ I_{\rm COM} = -100 \mbox{ mA}, \end{array}$	Switch ON, See Figure 14	25°C			0.5		
flatness	r _{on(flat)}	$V_{NO} \text{ or } V_{NC} = 0.8 \text{ V}, 1 \text{ V}, 1.8 \text{ V},$	Switch ON,	25°C	2.25 V		0.25	0.5	Ω
		$I_{\rm COM} = -100 \text{ mA},$	See Figure 14	Full				0.6	
		$V_{NO} = 0.5 V, 2.2 V,$		25°C		-20	2	20	
NO, NC OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}		Switch OFF, See Figure 15	Full	2.75 V	-50		50	nA
		$V_{NO} = 0.5 V, 2.2 V,$		25°C		-10	2	10	
NC, NO ON leakage current	I _{NO(ON)}	$\label{eq:VNC} \begin{array}{l} V_{NC} \text{ and } V_{COM} = \text{Open}, \\ \text{or} \\ V_{NC} = 2.2 \text{ V}, \ 0.5 \text{ V}, \\ V_{NO} \text{ and } V_{COM} = \text{Open}, \end{array}$	Switch ON, See Figure 16	Full	2.75 V	-20		20	nA
		$V_{COM} = 0.5 V,$		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$\label{eq:VNO} \begin{array}{l} V_{NO} \text{ and } V_{NC} = \text{Open}, \\ \text{or} \\ V_{COM} = 2.2 \text{ V}, \\ V_{NO} \text{ and } V_{NC} = \text{Open}, \end{array}$	Switch ON, See Figure 16	Full	2.75 V	-20		20	nA
Digital Control Input (IN) ⁽²⁾				1	1			
Input logic high	V _{IH}	$V_{IO} = 1.65 \text{ V to } 1.95 \text{ V}$		Full		0.65 × V _{IO}		V _{IO}	V
Input logic low	V _{IL}	V_{IO} = 1.65 V to 1.95 V		Full		0		0.35 × V _{IO}	V
Input leakage current	I _{IH} , I _{IL}	$V_{I} = V_{IO} \text{ or } 0$		25°C Full	2.75 V	-2 -20		2 20	nA

(1)

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, (2) Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

TS5A6542

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Electrical Characteristics for 2.5-V Supply (continued)

V₊ = 2.25 V to 2.75 V, V_{IO} = 1.65 V to 1.95 V, $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	۷,	MIN	TYP	MAX	UNIT
Dynamic			L.			1			
Turn-on time	+	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	2.5 V	5	20	35	20
rum-on time	t _{ON}	$R_L = 50 \Omega$,	See Figure 18	Full	2.25 V	5		40	ns
Turn-off time	+	$V_{COM} = V_+,$	C _L = 35 pF,	25°C	2.5 V	2	10	20	ns
rum-on ume	t _{OFF}	$R_L = 50 \Omega$,	See Figure 18	Full	2.25 V	2		25	115
Break-before-make	t	$V_{NC} = V_{NO} = V_{+}/2,$	C _L = 35 pF,	25°C	2.5 V	1	11	20	ns
time	t _{BBM}	$R_L = 50 \Omega$,	See Figure 19	Full	2.25 V	1		25	115
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 23	25°C	2.5 V		5		рС
NO OFF capacitance	C _{NO(OFF)}	$V_{NO} = V_+ \text{ or GND},$ Switch OFF,	See Figure 17	25°C	2.5 V		38		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	2.5 V		135		pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_{+} \text{ or GND},$ Switch ON,	See Figure 17	25°C	2.5 V		135		pF
Digital input capacitance	Cı	$V_{I} = V_{IO} \text{ or } GND,$	See Figure 17	25°C	2.5 V		6.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	2.5 V		40		MHz
OFF isolation	O _{ISO}	$\begin{array}{l} R_{L}=50\ \Omega,\\ f=1\ MHz, \end{array}$	See Figure 21	25°C	2.5 V		-63		dB
Crosstalk	X _{TALK}	$\begin{array}{l} R_{L}=50\ \Omega,\\ f=1\ MHz, \end{array}$	See Figure 22	25°C	2.5 V		-63		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	2.5 V		0.00 8		%
Supply									
Positive supply		V _I = V _{IO} or GND		25°C	2.75 V		10	25	25 nA
current	I+			Full	2.75 V			100	11/4

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TYPICAL PERFORMANCE

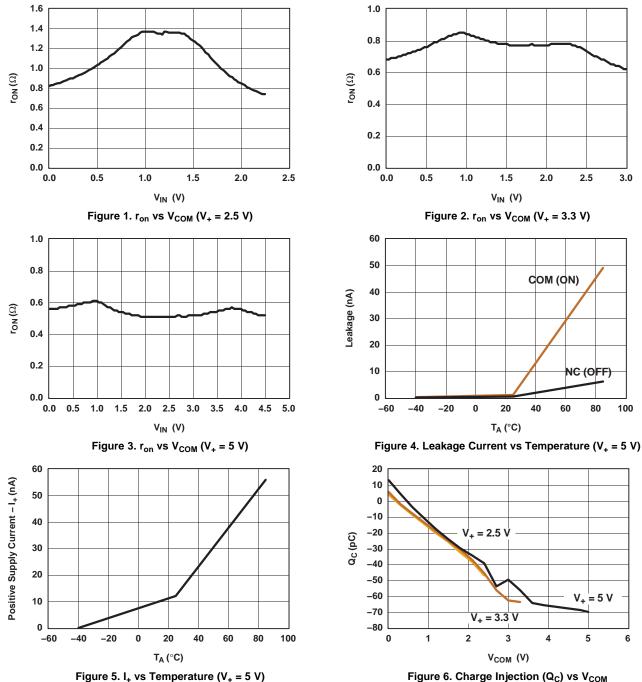
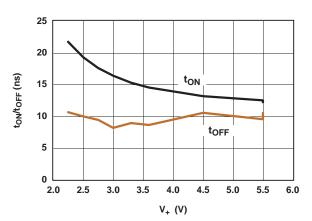


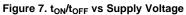
Figure 6. Charge Injection (Q_C) vs V_{COM}

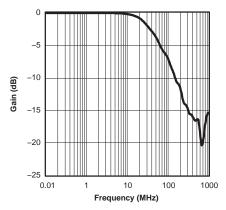


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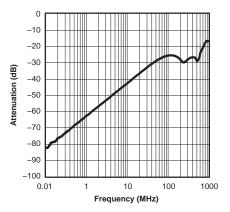
TYPICAL PERFORMANCE (continued)

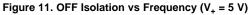












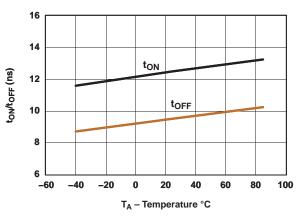


Figure 8. t_{ON}/t_{OFF} vs Temperature (V₊ = 5 V)

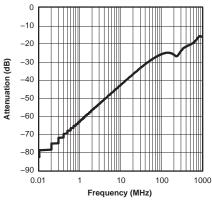


Figure 10. Crosstalk vs Frequency (V₊ = 5 V)

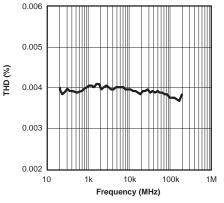
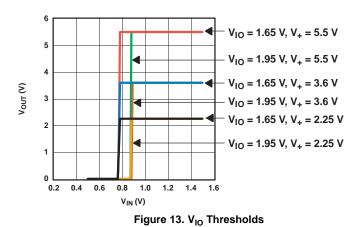


Figure 12. Total Harmonic Distortion vs Frequency (V_+ = 2.5 V)









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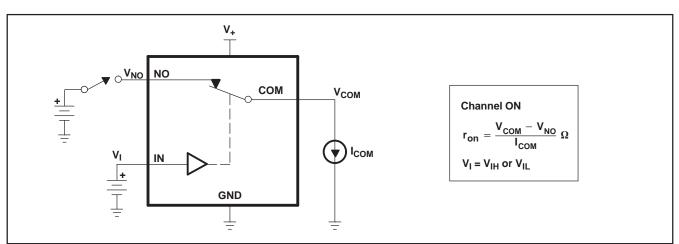


Figure 14. ON-State Resistance (ron)

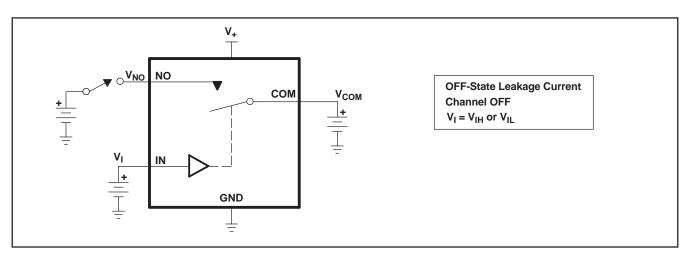
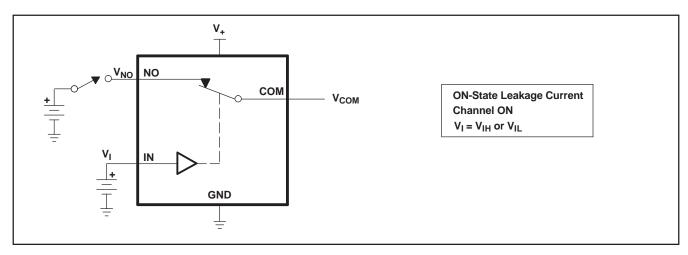
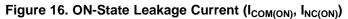


Figure 15. OFF-State Leakage Current (I_{COM(OFF)}, I_{NC(OFF)}, I_{COM(PWROFF)}, I_{NC(PWR(FF)})





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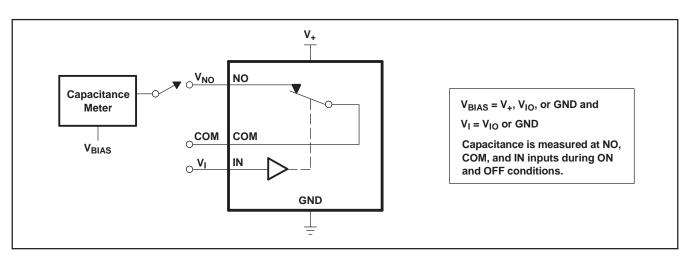
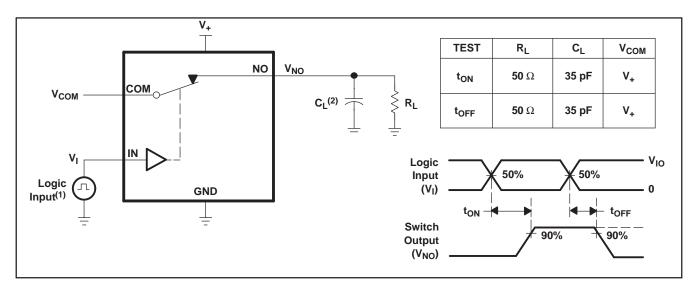


Figure 17. Capacitance (C_I, C_{COM(OFF)}, C_{COM(ON)}, C_{NC(OFF)}, C_{NC(ON)})



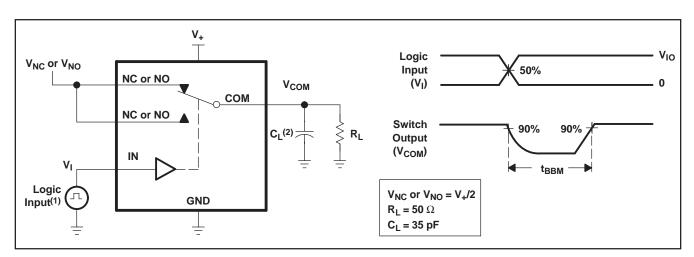
 $^{(1)}$ All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns. $^{(2)}$ C_L includes probe and jig capacitance.

Figure 18. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})





PARAMETER MEASUREMENT INFORMATION (continued)



⁽¹⁾ All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns. ⁽²⁾ C_L includes probe and jig capacitance.

Figure 19. Break-Before-Make Time (t_{BBM})

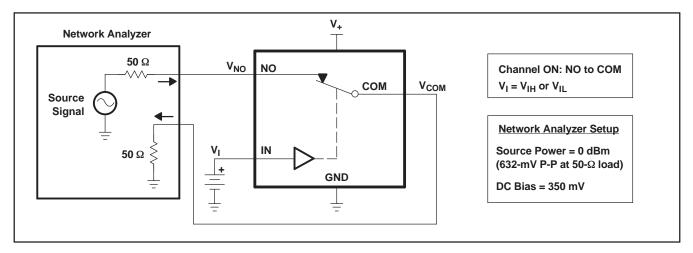


Figure 20. Bandwidth (BW)

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PARAMETER MEASUREMENT INFORMATION (continued)

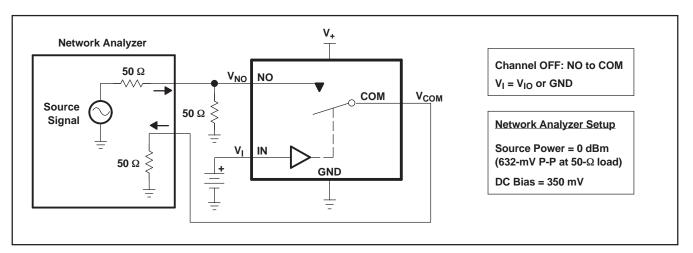


Figure 21. OFF Isolation (O_{ISO})

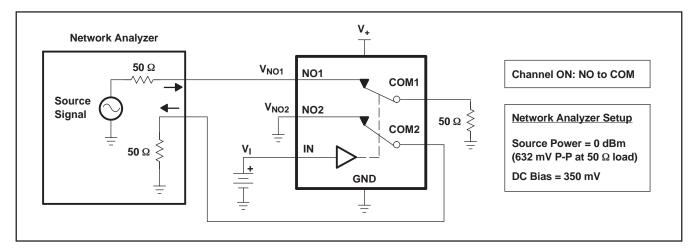
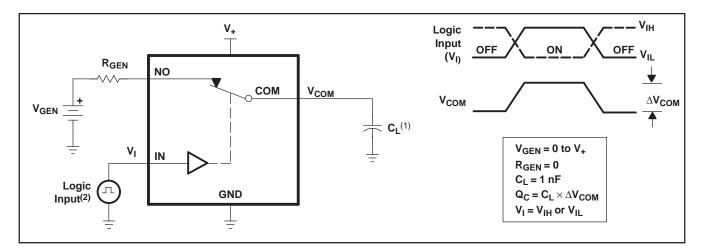


Figure 22. Crosstalk (X_{TALK})



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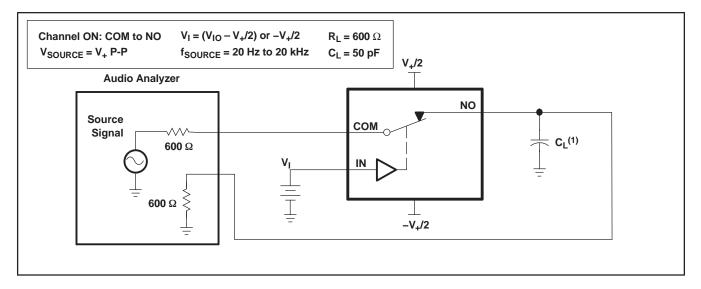




 $^{(1)}$ C_L includes probe and jig capacitance.

⁽²⁾ All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_f < 5 ns, t_f < 5 ns.

Figure 23. Charge Injection (Q_C)



 $^{(1)}\,$ CL includes probe and jig capacitance.

Figure 24. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins P	ackage Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TS5A6542YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



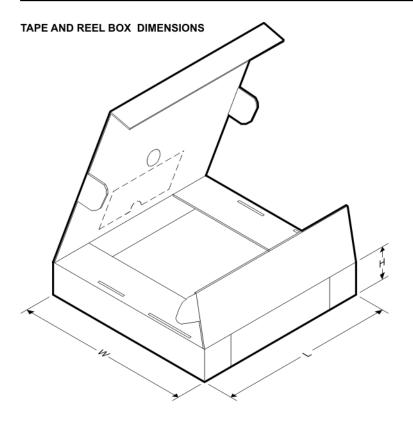
*All dimensions	are	nominal
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Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A6542YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.1	2.1	0.56	4.0	8.0	Q1



PACKAGE MATERIALS INFORMATION

22-Jul-2008

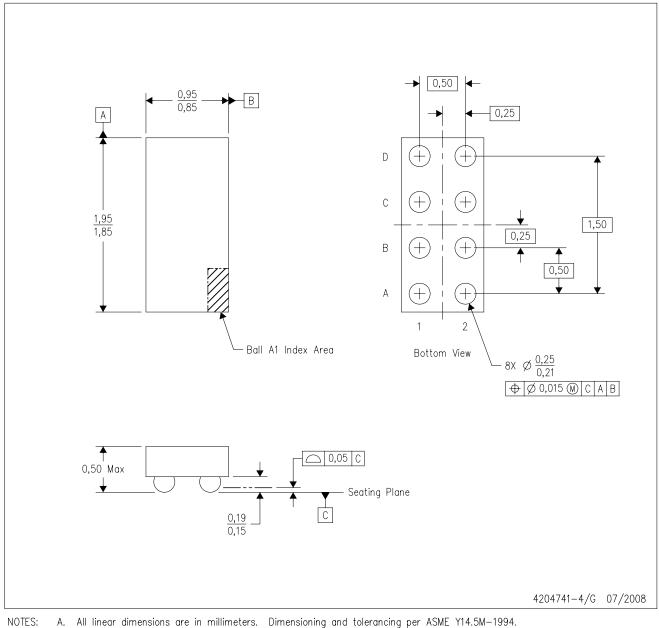


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A6542YZPR	DSBGA	YZP	8	3000	220.0	220.0	34.0

YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

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